

P18LA12SL

Power MOSFETs

120V, 18A, N-channel

Feature

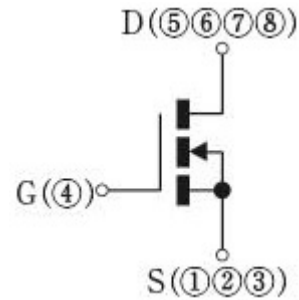
- N-channel
- Small SMD
- Low Ron
- 4.5V Gate Drive
- Low Capacitance
- Halogen free
- Pb free terminal
- RoHS:Yes

OUTLINE

Package (House Name): LA



Equivalent circuit



Absolute Maximum Ratings (unless otherwise specified : Tc=25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage temperature	Tstg		-55 to 150	°C
Channel temperature	Tch		-55 to 150	°C
Drain-source voltage	V _{DSS}		120	V
Gate-source voltage	V _{GSS}		±20	V
Continuous drain current(DC)	I _D		18	A
Continuous drain current(Peak)	I _{DP}	Pulse width 10μs, duty=1/100	54	A
Total power dissipation	P _T		99	W
Single avalanche current	I _{AS}	Starting Tch=25°C Tch≤150°C	18	A
Single avalanche energy	E _{AS}	Starting Tch=25°C Tch≤150°C	43	mJ

※ :See the original Specifications

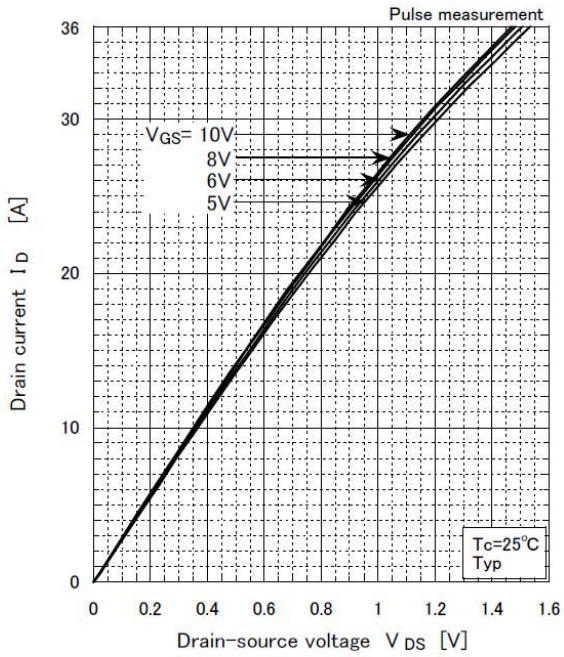
Electrical Characteristics (unless otherwise specified : Tc=25°C)

Item	Symbol	Conditions	Ratings			Unit
			MIN	TYP	MAX	
Drain-Source breakdown voltage	$V_{(BR)DSS}$	ID=1mA, VGS=0V	120			V
Zero gate voltage drain current	I_{DSS}	VDS=120V, VGS=0V			1	μ A
Gate-source leakage current	I_{GSS}	VGS= \pm 20V, VDS=0V			\pm 0.1	μ A
Forward transconductance	g_{fs}	ID=9A, VDS=10V	9			S
Static drain-source on-state resistance	$R_{DS(ON)}$	ID=9A, VGS=10V		0.035	0.044	Ω
Static drain-source on-state resistance	$R_{DS(ON)}$	ID=9A, VGS=4.5V		0.037	0.05	Ω
Gate threshold voltage	V_{th}	ID=1mA, VDS=10V	1.5	2	2.5	V
Source-drain diode forward voltage	V_{SD}	IS=18A, VGS=0V			1.5	V
Thermal resistance	$R_{th(j-c)}$	Junction to case, with heatsink			1.26	$^{\circ}$ C/W
Total gate charge	Q_g	VDD=96V, VGS=10V, ID=18A		47		nC
Gate to source charge	Q_{gs}	VDD=96V, VGS=10V, ID=18A		8.3		nC
Gate to drain charge	Q_{gd}	VDD=96V, VGS=10V, ID=18A		12		nC
Input capacitance	C_{iss}	VDS=25V, VGS=0V, f=1MHz		2090		pF
Reverse transfer capacitance	C_{rss}	VDS=25V, VGS=0V, f=1MHz		73		pF
Output capacitance	C_{oss}	VDS=25V, VGS=0V, f=1MHz		140		pF
Turn-on delay time	$t_{d(on)}$	ID=9A, RL=6.7 Ω , VDD=60V, Rg=0 Ω , VGS(+)=10V, VGS(-)=0V		4.3		ns
Rise time	t_r	ID=9A, RL=6.7 Ω , VDD=60V, Rg=0 Ω , VGS(+)=10V, VGS(-)=0V		6.6		ns
Turn-off delay time	$t_{d(off)}$	ID=9A, RL=6.7 Ω , VDD=60V, Rg=0 Ω , VGS(+)=10V, VGS(-)=0V		32		ns
Fall time	t_f	ID=9A, RL=6.7 Ω , VDD=60V, Rg=0 Ω , VGS(+)=10V, VGS(-)=0V		11		ns
Diode reverse recovery time	t_{rr}	IF=18A, VGS=0V, di/dt=100A/ μ s		57		ns
Diode reverse recovery charge	Q_{rr}	IF=18A, VGS=0V, di/dt=100A/ μ s		120		nC

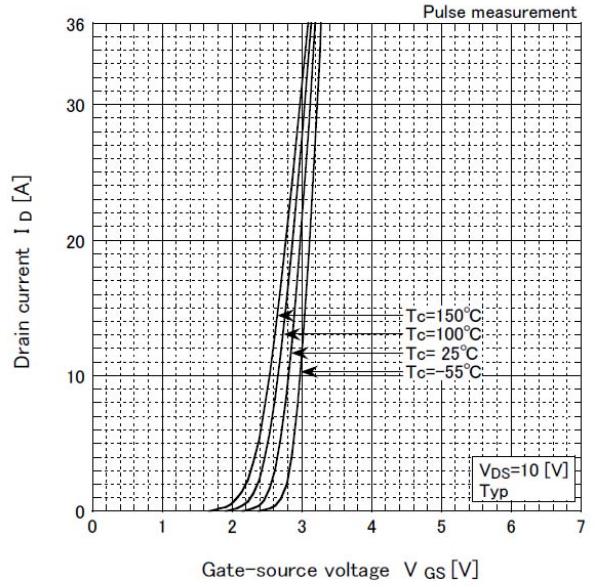
* : See the original Specifications

CHARACTERISTIC DIAGRAMS

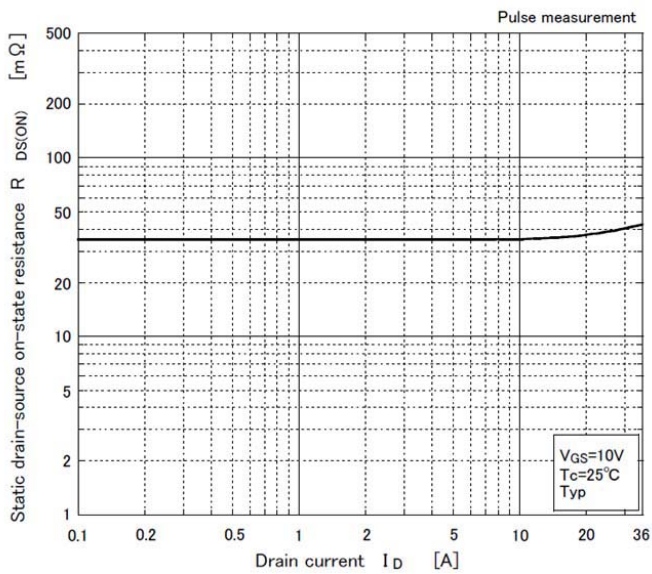
Typical output characteristics



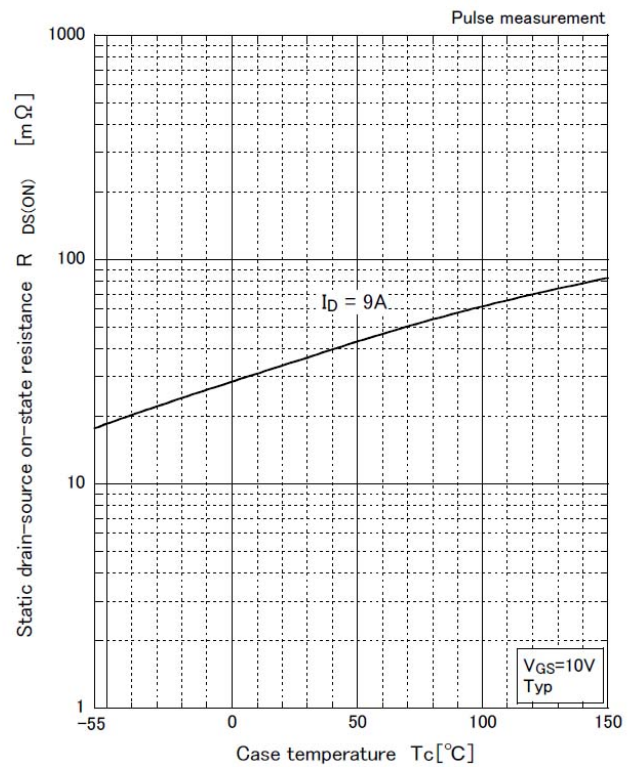
Transfer characteristics

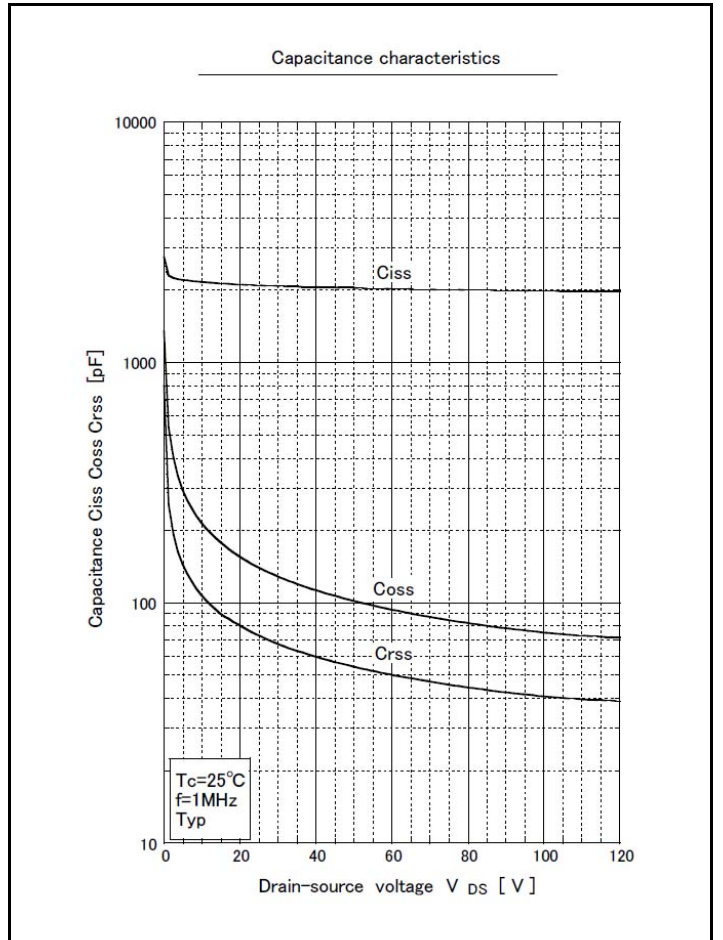
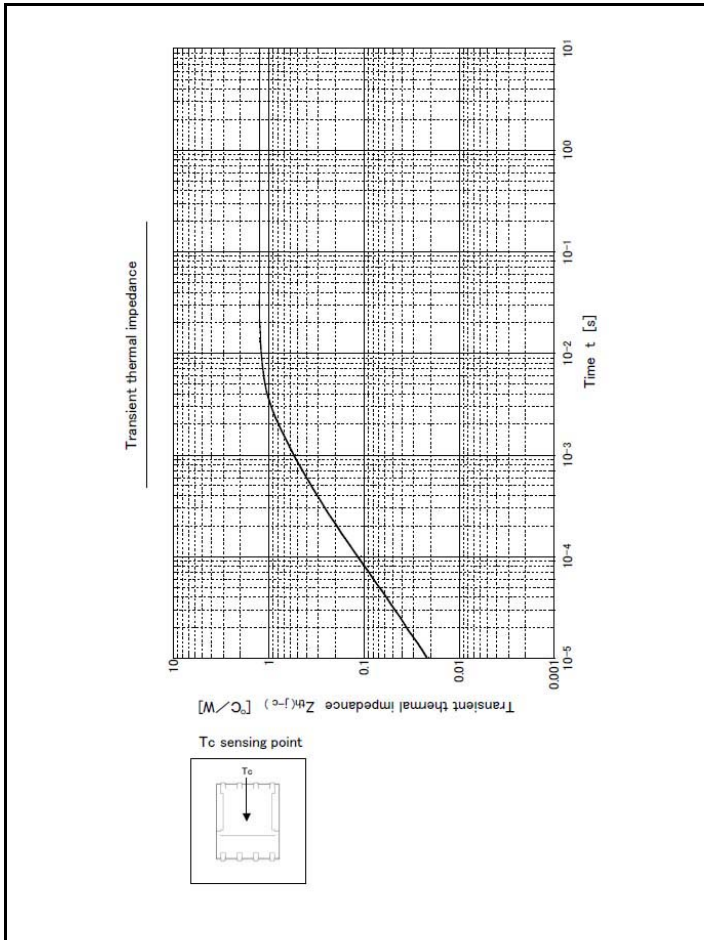
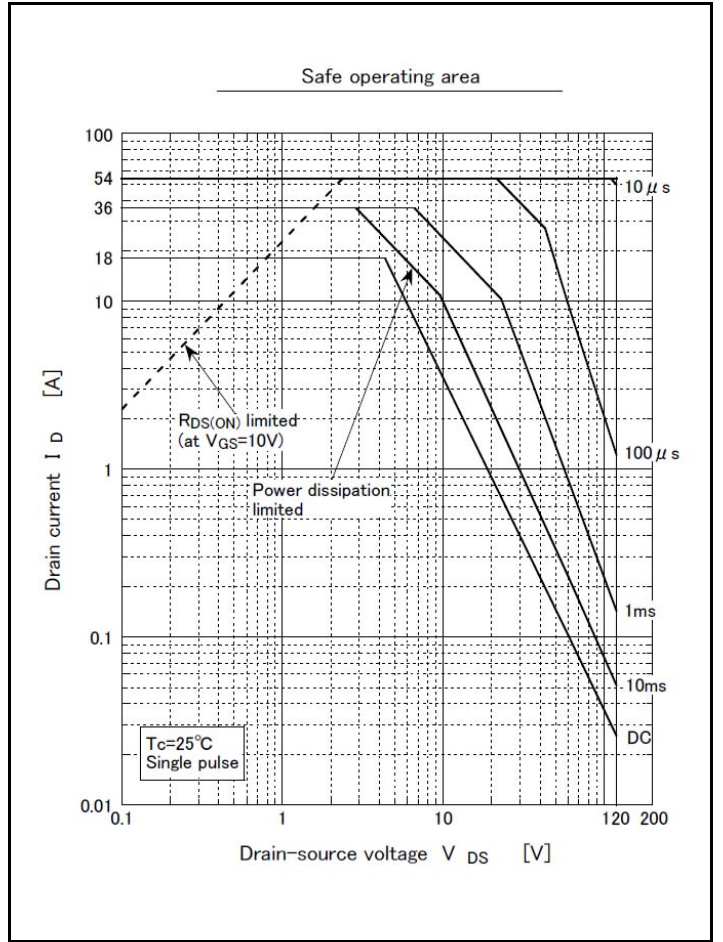
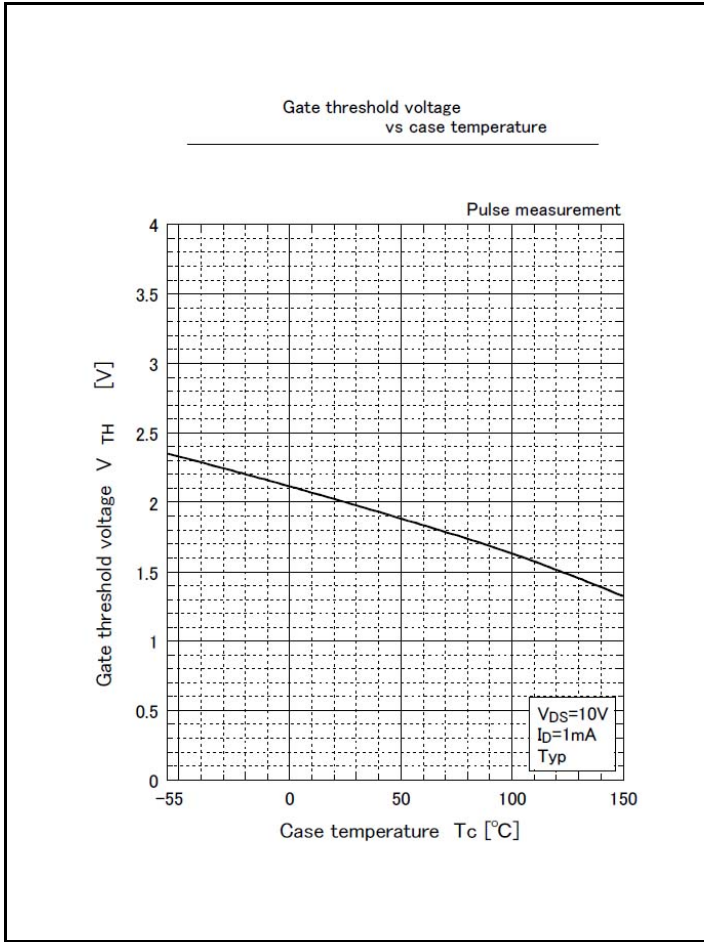


Static drain-source on-state resistance vs drain current

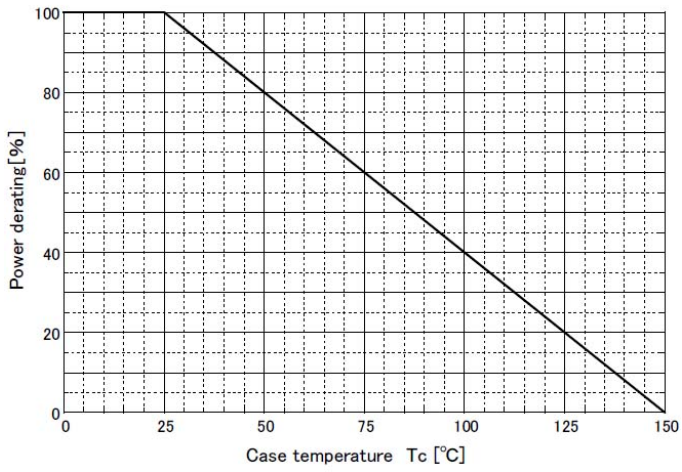


Static drain-source on-state resistance vs case temperature

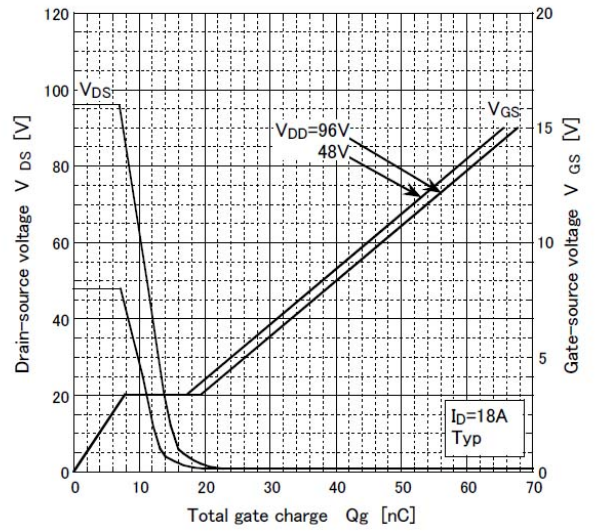




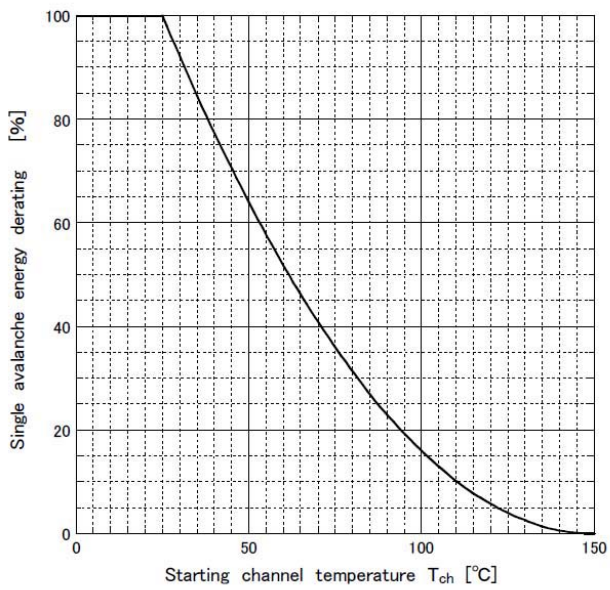
Power derating - case temperature



Gate charge characteristics



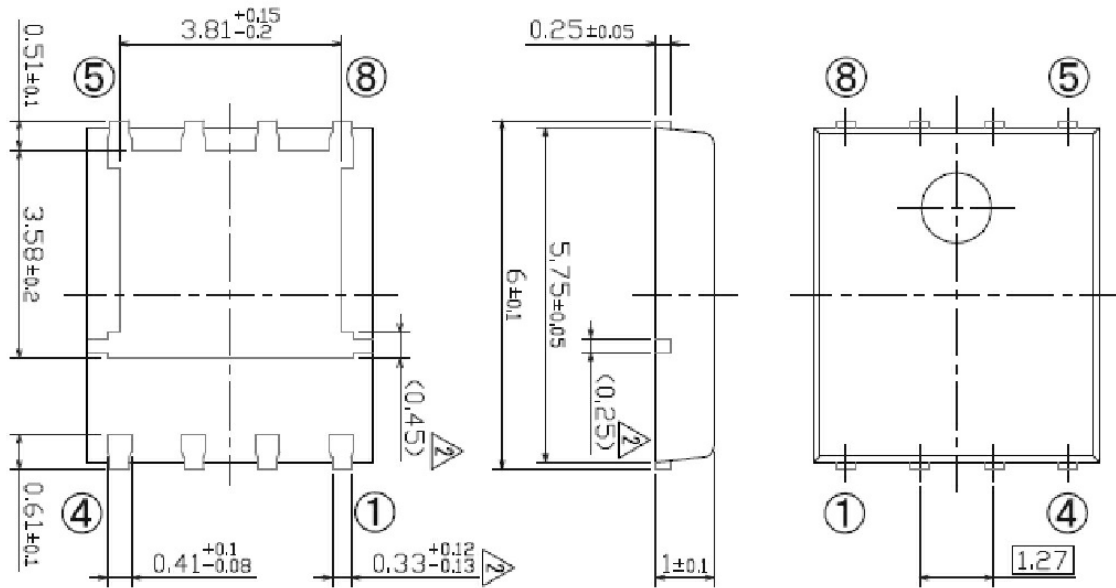
Single avalanche energy derating vs channel temperature



Outline Dimensions

unit:mm

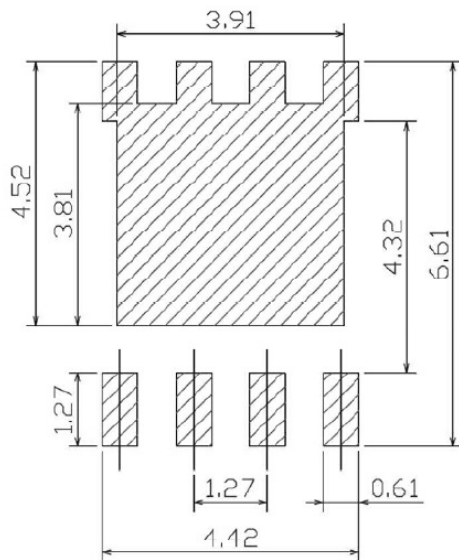
UNIT: mm



2. 端子配置 Lead Assignment

MOS-FET
 ①②③ : Source
 ④ : Gate
 ⑤⑥⑦⑧ : Drain

3. 製品質量: 0.09g(標準)
 Package Weight: 0.09g(typ)



Notes

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